

TN6727A



PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1A. Sourced from Process 77. See TN6726A for characteristics.

Absolute Maximum Ratings* TA = 25°C u

| Symbol | Parameter | Value | Units |
|----------------------|--------------------------------------------------|-------------|-------|
| V _{CES} | Collector-Emitter Voltage | 40 | V |
| V _{CBO} | Collector-Base Voltage | 50 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| I _C | Collector Current - Continuous | 1.5 | Α |
| T _{J, Tstg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

Thermal Characteristics ___ T_A = 25 °C unless otherwise noted

| Symbol | Characteristic | Max | Units |
|-------------------|-------------------------------------------------|---------|------------|
| | | TN6727A | |
| P _D | Total Device Dissipation 1 Derate above 25 °C 8 | | W mW/°C |
| R ₀ JC | Thermal Resistance, Junction to Case 50 | | °C/W |
| R _θ JA | Thermal Resistance, Junction to Ambient | 125 | °C/W |

¹⁾ These ratings are based on a maximum junction temperature of 150°C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

 $T_{A\,=\,25\,^{\circ}\text{C}}\,\,\text{unless otherwise noted}$

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|----------------------|--------------------------------------|---------------------------------------------------------------------------------------------------------------------------------|----------------|-----|-------|
| OFF CHA | RACTERISTICS | | • | | |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C = 10 mA | 40 | | V |
| BV _{CBO} | Collector-Base Breakdown Voltage | I _C = 1 mA | 50 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | I _E = 1 mA | 5 | | V |
| І _{СВО} | Collector Cutoff Current | V _{CB} = 50 V | | 100 | nA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5 V | | 100 | nA |
| ON CHAF | RACTERISTICS* | | | | |
| h _{FE} | DC Current Gain | $I_{C} = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 1A, V_{CE} = 1 \text{ V}$ | 55 60 50 | 250 | - |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 1 A, I _B = 100 mA | | 0.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 1 A, V _{CE} = 1 V | | 1.2 | V |
| SMALL SI | GNAL CHARACTERISTICS | | | | |
| C _{cb} | Output Capacitance | V _{CB} = 10 V, I _E = 0, f = 1MHz | | 30 | pF |
| h _{fe} | Small Signal Current Gain | I _C = 50 mA,V _{CE} = 10 V, f=20MHz | 2.5 | 25 | - |
| | <u> </u> | 1 | | | |

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1.0%

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